Initial Test Results for the Hamamatsu LumiCal Silicon Sensors

Iftach Sadeh on behalf of

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Silicon sensor

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Overview

Preliminary measurements were performed on the Hamamatzu silicon sensors:

- Several pads from one sensor were tested.
- The tests included several kinds of I/V measurements as well as C/V measurements.



Overview

At the design stage we take into account:

- results of Monte Carlo studies on angular resolution
- available (standard) silicon sensor technology
- requirement of FE electronics, number of channels and cost
- possible improvement of shower reconstruction accuracy by simple increase pads granularity (e.g. azimuth)
- remarks from Hamamatsu engineers







Top Layer & Dimensions

Segmentation of 4 sectors they were produced by Hamamatsu

Details of the structure: gap between tiles and guard rings

Detector description

Hamamatsu S10938-8380



"Cracow-Design"

- High resistivity n-type Si
- 1,7mm p+ strips with an Al-metallization
- Backplane: n+ implant and an Al-metallization
- 3 Guard rings
- x-Size = 10,8cm y-Size = 4...12cm (6 Inch Wafers)

I/V Measurements



Courtesy of W. Lange

I/V curves -Sensor damage

One of the Sensors was damaged during the measurements. The scratch in the area of the guard ring had no affect on the padcurrent, but the guardring current spiked.





inner guard ring

I/V curves – Grounding issues

• The measurement setup is extremely sensitive to grounding.

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 The plot shows an I/V measurement before and after grounding of the probstation box

I/V Pad - box grounded - L2 Ch46



Scale 1:1 Top Layer

> 4 segments of the detector

L1 R1

12

Channel 1

Channel 64



I/V curves

 Measurements were performed by our student both at DESY-Zeuthen (top right figure) and at Tel-Aviv (bottom figures) on different sensors, but on the same pads.

4 segmen

of the detector

Scale 1:1 Top Layer



Voltage [V]

Channel 64

Channel 1

I/V curves for different temperature & humidity

10

 Measurements were performed on the same pad with different external conditions, defined in the plot as:



I/V curves for different connection points

- Measurements were performed on the same pad on the two different connectors, showing slightly different results (~0.3 nA) between the right and left connectors.
- The difference may be due to the vicinity to the gouard ring.



I/V curves with one/two neighbors grounded



¹³ I/V curves with two neighbors grounded



L2

L1

C/V Measurements

Keithley 6487 (Voltage Source)



Bias Adapter Scheme



Courtesy of W. Lange

C/V & Depletion Voltage Measurement

The full depletion voltage is determined by the voltage in which the capacitance saturates.

In these measurements the saturation is not full due to the fact that our sensor is not ideal. So the full depletion voltage is determined to be the cross point between two linear fits:

one for the part of the curve where the capacitance decrease,
the second for the "saturation"

• the second for the saturation part of the curve.

Results in both labs give ~ 42 Volt as the depletion voltage

R. Schwartz at Desy-Zeuthen



Summary

- The preliminary measurements produce similar results to the DESY-Zeuthen tests for the C/V measurement and for the I/V pad-current measurements.
- Grounding is a major issue; additional I/V measurements need to be performed with grounding of more neighboring pads.
- For the near future we plan:
 - A full set of tests on all pads in all sensor planes.
 - Comprehensive temperature and humidity dependent I/V curves.

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